

BRCS045N10SHRA

Rev.A Feb.-2023

描述 / Descriptions

TO-220 N

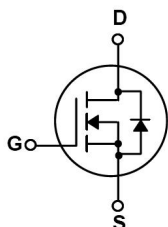
N-CHANNEL MOSFET in a TO-220 Plastic Package.

特点 / Features

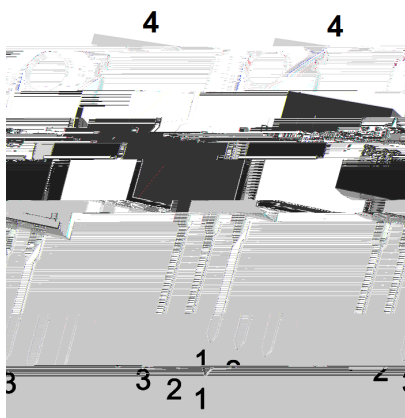
应用 / Applications

High frequency switching and synchronous rectification, BMS, Motor.

等效电路 / Equivalent Circuit



引脚 / Pinning



PIN1 G

PIN 2 4 D

PIN 3 S\

标记 / Marking

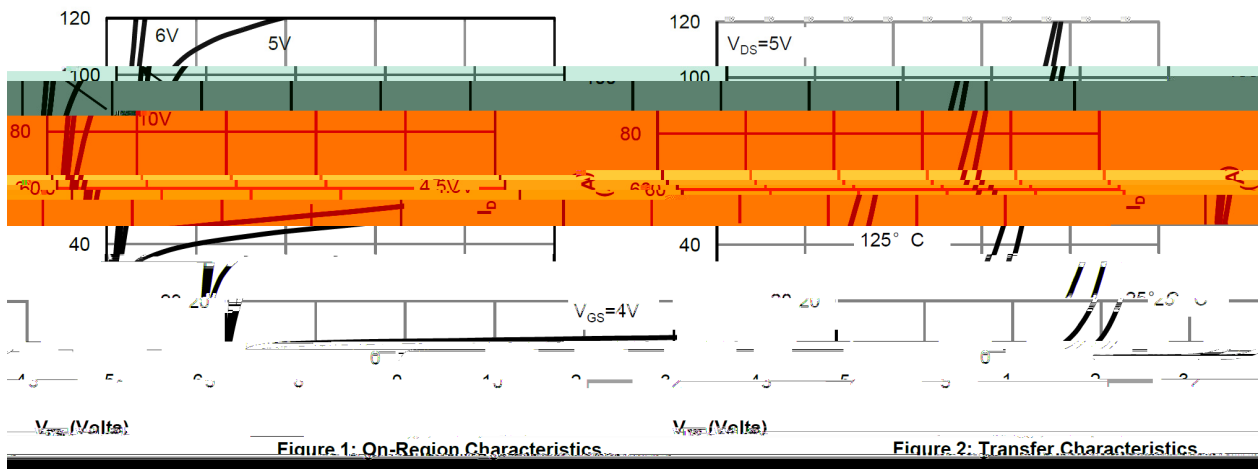
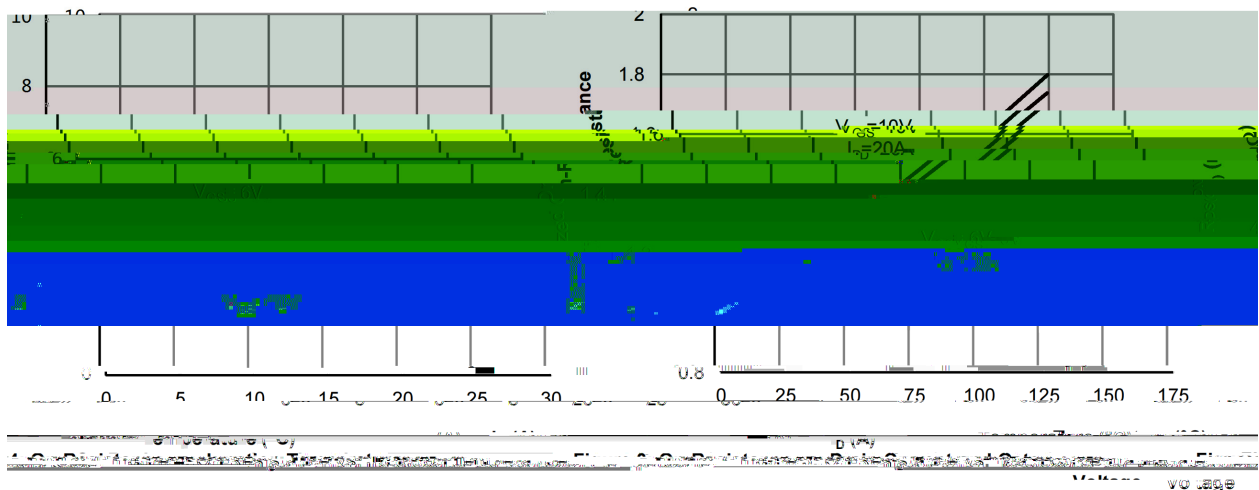
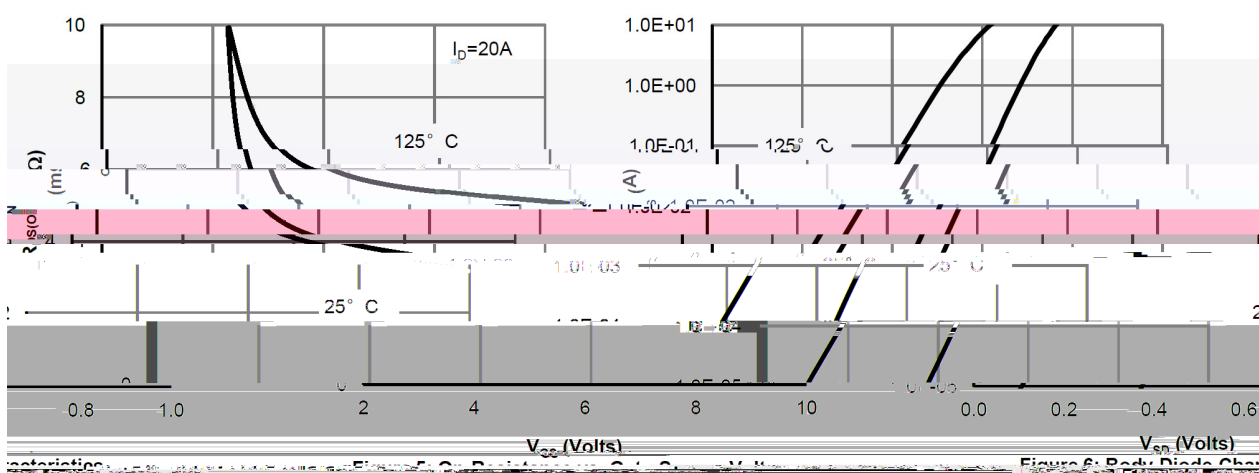
See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	150	A
Pulsed Drain Current		I_{DM}	319	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	381	mJ
Avalanche Current		I_{AS}	33	A
Total Power Dissipation		$P_D(T_c=25^\circ\text{C})$	180	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	17	/W
	Steady-State		62.5	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.69	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	2.6	4	V
Static Drain-Source On-Resistance	$R_{DS(on)1}$	$V_{GS}=10V$ $I_D=20A$		3.2	4.5	$m\Omega$
	$R_{DS(on)2}$	$V_{GS}=6V$ $I_D=10A$		4.2	6.5	$m\Omega$
Forward On Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Gate resistance	R_g	$f=1MHz$		1.3		Ω

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $R_L=2.5\Omega$ $V_{DS}=50V$ $R_{GEN}=3\Omega$		27		ns
Turn-On Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(of)}$					

Electrical Characteristic Curve



一、产品概述

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蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

4. 1. 1 / Marking Instructions

